Electronic properties of graphene - II

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Monolayer graphene



Band structure of bilayer graphene, 'chiral' electrons and Berry's phase 2π .

Effect of trigonal warping and the Lifshitz transition.

Landau levels and the quantum Hall effect in bilayer and monolayer graphene.

Interlayer asymmetry gap in bilayers.



Bilayer [Bernal (AB) stacking]





Bilayer [Bernal (AB) stacking]



In the vicinity of each of K points

$$\begin{array}{cccc} (\text{B to A}) \text{ and } (\widetilde{B} \text{ to } \widetilde{A}) & A & \widetilde{B} & \widetilde{A} & B \\ & \text{hopping} & & \\ & \text{given by} & H = \begin{pmatrix} & & \nu \pi^+ \\ & \nu \pi & & \\ & \nu \pi^+ & & \end{pmatrix} \begin{array}{c} A & \widetilde{B} & \widetilde{A} & B \\ & \widetilde{B} & \widetilde{A} \\ & \widetilde{B} & \widetilde{A} \\ & V \pi^+ & & & \\ & V \pi & & & \end{array} \right) \begin{array}{c} A & \widetilde{B} & \widetilde{A} & B \\ & \widetilde{B} & \widetilde{A} \\ & \widetilde{B} & \widetilde{A} \end{array}$$

Bilayer [Bernal (AB) stacking]



In the vicinity of each of K points









$$\hat{H}_{2} = \frac{-1}{2m} \begin{pmatrix} 0 & (\pi^{+})^{2} \\ \pi^{2} & 0 \end{pmatrix} = \frac{-p^{2}}{2m} \begin{pmatrix} 0 & e^{-2i\varphi} \\ \pi^{-2i\varphi} & 0 \end{pmatrix} = \frac{-p^{2}}{2m} \vec{n} \cdot \vec{\sigma}$$

$$\pi = p_x + ip_y = pe^{i\phi}$$
$$\pi^+ = p_x - ip_y = pe^{-i\phi}$$

$$\vec{n}(\vec{p}) = (\cos 2\varphi, \sin 2\varphi)$$



$$\psi \to e^{2 \times 2\pi \frac{i}{2}\sigma_3} \psi = e^{i2\pi} \psi$$

Berry phase 2π

(for a monolayer = π) Monolayer: $H = v\xi \begin{pmatrix} 0 & \pi^+ \\ \pi & 0 \end{pmatrix}$



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$$\hat{H}_{2} = -\frac{1}{2m} \left[\sigma_{x} \left(p_{x}^{2} - p_{y}^{2} \right) + \sigma_{y} \left(p_{x} p_{y} + p_{y} p_{x} \right) \right] \\ + v_{3} \left(\sigma_{x} p_{x} - \sigma_{y} p_{y} \right) \\ \text{'trigonal warping'} \\ \text{Berry phase:} \\ 2\pi = 3\pi - \pi \\ \text{weak magnetic field} \\ \lambda_{B}^{-1} \sim p < mv_{3} \\ \text{strong magnetic field} \\ \lambda_{B}^{-1} \sim p >> mv_{3} \\ \text{strong magnetic field} \\ \lambda_{B}^{-1} \sim p >> mv_{3} \\ \text{weak magnetic field} \\ \lambda_{B}^{-1} \sim p >> mv_{3} \\ \text{strong magnetic field} \\ \lambda_{B}^{-1} \sim p >> mv_{3} \\ \text{strong magnetic field} \\ \lambda_{B}^{-1} \sim p >> mv_{3} \\ \text{strong magnetic field} \\ \lambda_{B}^{-1} \sim p >> mv_{3} \\ \text{strong magnetic field} \\ \lambda_{B}^{-1} \sim p >> mv_{3} \\ \text{strong magnetic field} \\ \lambda_{B}^{-1} \sim p >> mv_{3} \\ \text{strong magnetic field} \\ \lambda_{B}^{-1} \sim p >> mv_{3} \\ \text{strong magnetic field} \\ N_{L} < N < 8N^{*} \\ N^{*} = \frac{\gamma_{1}^{2}}{4\pi\hbar^{2}v^{2}} \sim 4 \times 10^{12} cm^{-2} \\ \text{strong magnetic field} \\ N_{L} = 2 \left(\frac{v_{3}}{v} \right)^{2} \frac{\gamma_{1}}{4\pi\hbar^{2}v^{2}} \sim 10^{11} cm^{-2} \\ \text{Lifshitz transition} \\ \text{strong magnetic field} \\ N_{L} = 2 \left(\frac{v_{3}}{v} \right)^{2} \frac{\gamma_{1}}{4\pi\hbar^{2}v^{2}} \sim 10^{11} cm^{-2} \\ \text{Lifshitz transition} \\ \text{strong magnetic field} \\ N_{L} = 2 \left(\frac{v_{3}}{v} \right)^{2} \frac{\gamma_{1}}{4\pi\hbar^{2}v^{2}} \sim 10^{11} cm^{-2} \\ \text{strong magnetic field} \\ N_{L} = 2 \left(\frac{v_{3}}{v} \right)^{2} \frac{\gamma_{1}}{4\pi\hbar^{2}v^{2}} \sim 10^{11} cm^{-2} \\ \text{strong magnetic field} \\ N_{L} = 2 \left(\frac{v_{3}}{v} \right)^{2} \frac{\gamma_{1}}{4\pi\hbar^{2}v^{2}} \sim 10^{11} cm^{-2} \\ \text{strong magnetic field} \\ N_{L} = 2 \left(\frac{v_{3}}{v} \right)^{2} \frac{\gamma_{1}}{4\pi\hbar^{2}v^{2}} = 10^{11} cm^{-2} \\ \text{strong magnetic field} \\ N_{L} = 2 \left(\frac{v_{3}}{v} \right)^{2} \frac{\gamma_{1}}{4\pi\hbar^{2}v^{2}} = 10^{11} cm^{-2} \\ \text{strong magnetic field} \\ N_{L} = 2 \left(\frac{v_{3}}{v} \right)^{2} \frac{\gamma_{1}}{4\pi\hbar^{2}v^{2}} = 10^{11} cm^{-2} \\ \text{strong magnetic field} \\ N_{L} = 2 \left(\frac{v_{3}}{v} \right)^{2} \frac{v_{3}}{4\pi\hbar^{2}v^{2}} = 10^{11} cm^{-2} \\ \text{strong magnetic field} \\ N_{L} = 10^{10} cm^{-2} \\ N_{L} = 10^{10} cm^{-2}$$

Summary of band structure: chiral electrons in monolayer and bilayer graphene

$$H_{1} = \varsigma v \begin{pmatrix} 0 & \pi^{+} \\ \pi & 0 \end{pmatrix} + \mu \begin{pmatrix} 0 & \pi^{2} \\ (\pi^{+})^{2} & 0 \end{pmatrix} \qquad \begin{pmatrix} A \\ B \\ B \\ \zeta = -1 \end{pmatrix}$$
valley
'trigonal warping' terms
$$H_{2} = \frac{1}{2m} \begin{pmatrix} 0 & (\pi^{+})^{2} \\ \pi^{2} & 0 \end{pmatrix} + \varsigma v_{3} \begin{pmatrix} 0 & \pi \\ \pi^{+} & 0 \end{pmatrix} \qquad \begin{pmatrix} A \\ \tilde{B} \\ \tilde{B} \\ \zeta = -1 \end{pmatrix}$$

dominant at a high magnetic field and in high-density structures

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Monolayer and bilayer graphene optics.

2D Landau levels

semiconductor QW / heterostructure (GaAs/AlGaAs)

$$\vec{p} = -i\hbar \nabla - \frac{e}{c}\vec{A}, \quad rot\vec{A} = B\vec{l}_z$$
$$\pi = p_x + ip_y; \quad \pi^+ = p_x - ip_y$$
$$\pi \varphi_0 = 0$$
$$\varphi_{n+1} = \frac{\lambda_B}{\sqrt{n+1}}\pi^+ \varphi_n$$

 $H = \frac{\vec{p}^2}{2m} = \frac{\pi \pi^+ + \pi^+ \pi}{4m} \Longrightarrow (n + \frac{1}{2})\hbar\omega_c \longleftarrow \text{ energies / wave functions}$







2D Landau levels of chiral electrons J=1 monolayer J=2 bilayer

$$g\begin{pmatrix} 0 & (\pi^{+})^{J} \\ \pi^{J} & 0 \end{pmatrix} \psi = \varepsilon \psi$$

$$\begin{pmatrix} \varphi_{0} \\ 0 \end{pmatrix}, \dots, \begin{pmatrix} \varphi_{J-1} \\ 0 \end{pmatrix} \Rightarrow \varepsilon = 0$$

$$\pi^J \varphi_0 = \ldots = \pi^J \varphi_{J-1} = 0$$

4J-degenerate zero-energy Landau level

valley index

$$\begin{pmatrix} 0 & (\pi^{+})^{J} & & \\ \pi^{J} & 0 & & \\ & 0 & (-\pi^{+})^{J} & \\ & (-\pi)^{J} & 0 & \end{pmatrix} \begin{pmatrix} A & + \\ \tilde{B} & + \\ \tilde{B} & - \\ A & - \end{pmatrix}$$

also, two-fold real spin degeneracy



Monolayer, J=1, Berry's phase π

McClure, Phys. Rev. 104, 666 (1956) Haldane, Phys.Rev.Lett. 61, 2015 (1988) Zheng, Ando Phys. Rev. B 65, 245420 (2002)

$$\varepsilon^{\pm} = \pm \sqrt{2n} \frac{v}{\lambda_B}$$

$$g \begin{pmatrix} 0 & (\pi^{+})^{J} \\ \pi^{J} & 0 \end{pmatrix} \psi = \varepsilon \psi$$

Bilayer, J=2, Berry's phase 2π $\mathcal{E}^{\pm} = \pm \hbar \omega_c \sqrt{n(n-1)}$

8-fold degenerate $\varepsilon = 0$ Landau level for electrons with degree of chirality J=2

McCann, VF - Phys. Rev. Lett. 96, 086805 (2006)









Unconventional quantum Hall effect and Berry's phase of 2π in bilayer graphene



How robust is the degeneracy of $\mathcal{E}_0 = \mathcal{E}_1 = 0$ Landau level in bilayer graphene?



Direct inter-layer $A\widetilde{B}$ hops (warping term, Lifshitz trans.)

$$\mathcal{E}_0 = \mathcal{E}_1$$

McCann, VF - PRL 96, 086805 (2006)





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Interlayer asymmetry gap in bilayer graphene

McCann, VF - PRL 96, 086805 (2006)

$$\hat{H}_{2} = -\frac{v^{2}}{\gamma_{1}} \begin{pmatrix} 0 & (\pi^{\dagger})^{2} \\ \pi^{2} & 0 \end{pmatrix} + \xi v_{3} \begin{pmatrix} 0 & \pi \\ \pi^{\dagger} & 0 \end{pmatrix} + \begin{pmatrix} \xi \Delta & 0 \\ 0 & -\xi \Delta \end{pmatrix} + \begin{pmatrix} \xi \Delta & 0 \\ 0 & -\xi \Delta \end{pmatrix}$$

T. Ohta *et al* – Science 313, 951 ('06) (Rotenberg's group at Berkeley NL)



Interlayer asymmetry gap in bilayer graphene

McCann, VF - PRL 96, 086805 (2006) McCann - cond-mat/0608221

$$\hat{H}_{2} = -\frac{v^{2}}{\gamma_{1}} \begin{pmatrix} 0 & (\pi^{\dagger})^{2} \\ \pi^{2} & 0 \end{pmatrix} + \xi v_{3} \begin{pmatrix} 0 & \pi \\ \pi^{\dagger} & 0 \end{pmatrix} + \begin{pmatrix} \xi \Delta & 0 \\ 0 & -\xi \Delta \end{pmatrix} + \begin{pmatrix} \xi \Delta & 0 \\ 0 & -\xi \Delta \end{pmatrix}$$

Band mini-gap in bilayer graphene can be controlled electrically, so that a bilayer graphene transistor can be driven into a pinched-off (insulating) state.

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 $\frac{2\pi e^2}{\hbar c}$ - < 5%

Why can one see graphene in an optical microscope?

Abergel, VF - PR B 75, 155430 (2007)

Graphene flakes are visible when the oxide layer in SiO₂/Si wafer acts as clearing optical film if

$$\frac{\lambda}{2} = \frac{\sqrt{\varepsilon_s - \sin^2 \alpha}}{N + \frac{1}{2}} s$$

visibility, $V = (R - R_0) / R_0$ 60 (a)Monolayer Bilayer 8.0 50 Thick oxidized Si slab Thick_300h Sinslab 0.6 [gab] -30 0.4 0.2 $\delta \alpha = 10^{\circ}$ 12 20 -0.2 Incident angle 1.2 (b) Bilayer Monolayer 0.8 SiC slab $s = 1 \mu m$ SiC slab 0.6 0.4 0.2 n $\delta \alpha = 10^{\circ}$ 20 -0.2 10 0.4 0.6 0.8 1 1.2 1.4 1.6 1.8 0.4 0.6 0.8 1.2 1.4 1.6 1.8 1 Frequency - [eV]





Abergel, Russell, VF - Appl. Phys. Lett. 91, 063125 (2007)

Blake, Hill, Castro Neto, Novoselov, Jiang, Yang, Booth, Geim - Appl. Phys. Lett. 91, 063124 (2007)